Recent progress in resistive random access memories: M and performance

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#	Article	IF	Citations
1	Operation methods of resistive random access memory. Science China Technological Sciences, 2014, 57, 2295-2304.	2.0	14
2	Set statistics in conductive bridge random access memory device with Cu/HfO2/Pt structure. Applied Physics Letters, 2014, 105, .	1.5	42
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6	Resistive switching and conductance quantization in Ag/SiO2/indium tin oxide resistive memories. Applied Physics Letters, 2014, 105, .	1.5	85
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8	Statistical characteristics of reset switching in Cu/HfO2/Pt resistive switching memory. Nanoscale Research Letters, 2014, 9, 2500.	3.1	16
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